



04-20-06

10/20/06

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Benjamin A. Haskell et al. Examiner: William D. Coleman
Serial No.: 10/537,644 Group Art Unit: 2823
Filed: June 6, 2005 Docket: G&C 30794.93-US-WO
Title: GROWTH OF REDUCED DISLOCATION DENSITY NON-POLAR GALLIUM NITRIDE BY HYDRIDE VAPOR PHASE EPITAXY

CERTIFICATE OF MAILING UNDER 37 CFR 1.10

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By: *Barbara Senty*
Name: Barbara Senty

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Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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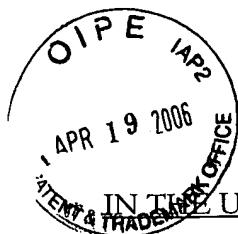
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INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(c))

MAIL STOP AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

Pursuant to 37 C.F.R. §1.97(c), please charge the amount of \$180.00 to Deposit Account No. 50-0494 of Gates & Cooper LLP for having the items of information listed considered after the mailing date of a first Office Action on-the-merits, but before the mailing date of either a final action under 37 C.F.R. § 1.113, or a Notice of Allowance under 37 C.F.R. § 1.311.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each foreign patent document and each non-patent document listed on the enclosed Form 1449 is provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102

and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that

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the reference(s) are not "prior art". Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please direct any response or inquiry to the below-signed attorney at (310) 641-8797.

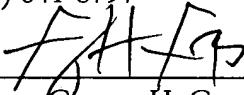
Respectfully submitted,

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Date: April 19, 2006

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U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,900,070	05/31/2005	Craven et al.			
	6,645,295	11/11/2003	Koike et al.			
	6,635,901	10/21/2003	Sawaki et al.			
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FOREIGN PATENTS						
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
	WO 2004/061969	07/22/2004	PCT			
	WO 2005/064643	07/14/2005	PCT			
	WO 2004/061909	07/22/2004	PCT			
	0 942 459	09/15/1999	Europe			
	2001 257166	09/21/2001	Japan (Abstract only)			
	2002 076329	03/15/2002	Japan (Abstract only)			
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NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

1	Wang, F. et al., "Crystal Tilting in the Epitaxial Laterally Overgrown GaN Films on Sapphire Substrate by Hydride Vapor Phase Epitaxy", Solid State and Integrated-Circuit Technology Proceedings, 6 th International Conference, October 2001, Vol. 2, pp. 1998-1201.
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75	Haskell et al., "Defect reduction in (1120) a-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor-phase epitaxy", <i>Applied Physics Letters</i> , Vol. 83 No. 4 (07/28/03)	
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79	Nam, Ok-Hyun et al., "Lateral epitaxy of low defect density GaN layers via organometallic vapor phase epitaxy", <i>Appl. Phys. Lett.</i> 71 (18) (11/03/97)	
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81	Yue Jun Sun et al., "Nonpolar In _x Ga _{1-x} N/GaN(1100) multiple quantum wells grown on γ -LiAlO ₂ (100) by plasma-assisted molecular-beam epitaxy", <i>Physical Review B</i> 67 (2003)	
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